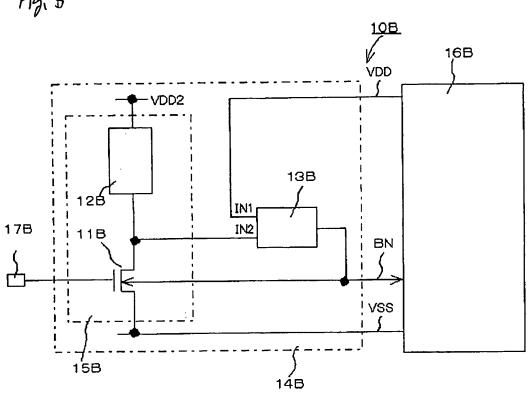
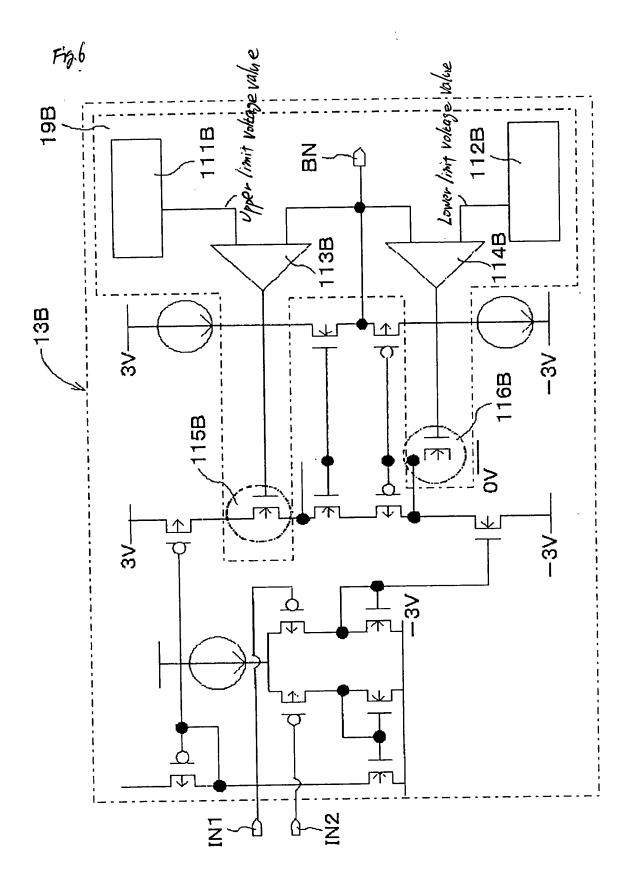
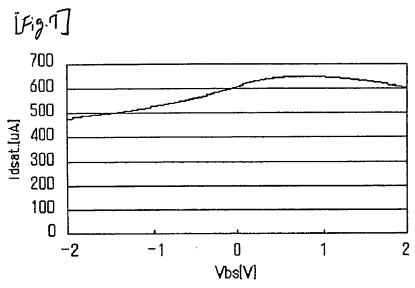


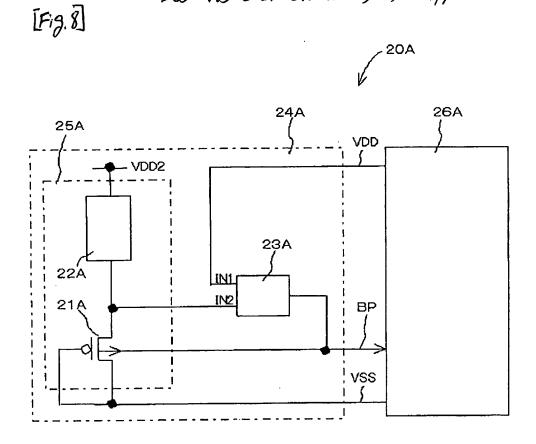
Fig. 5



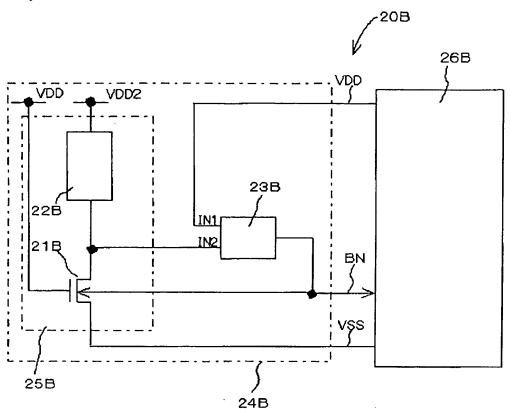


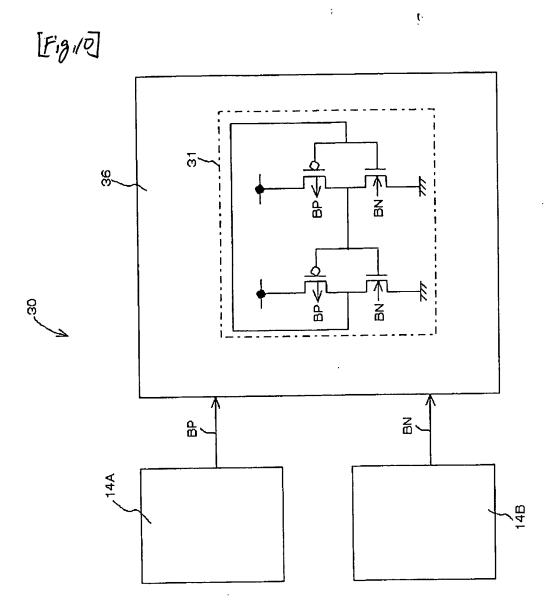


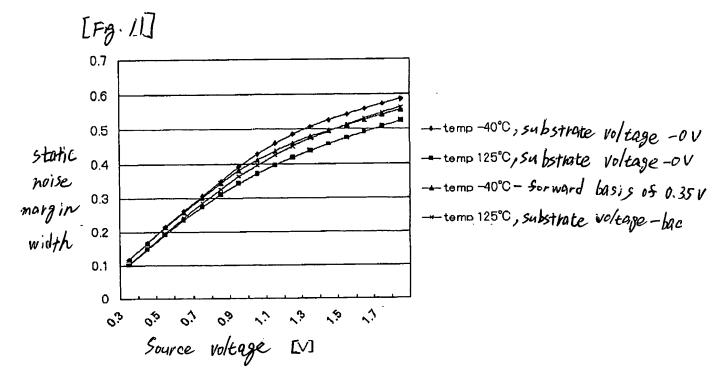
Ids-Vbs characteristics of n-type Mos FET

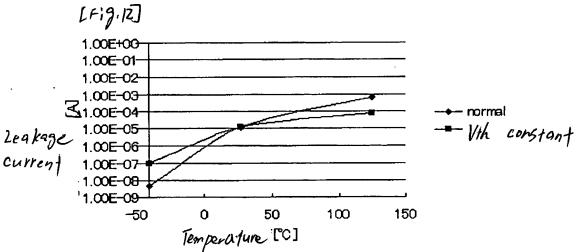




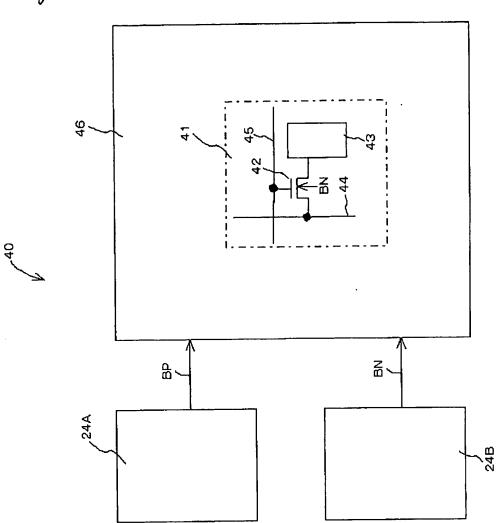




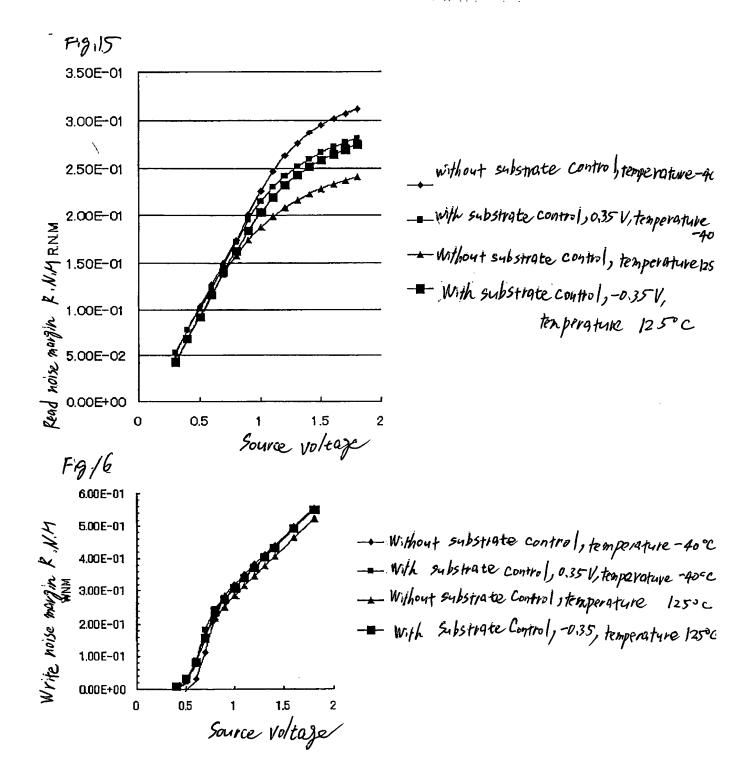


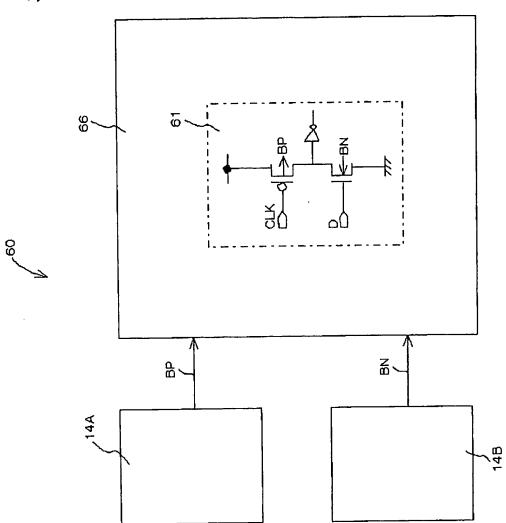


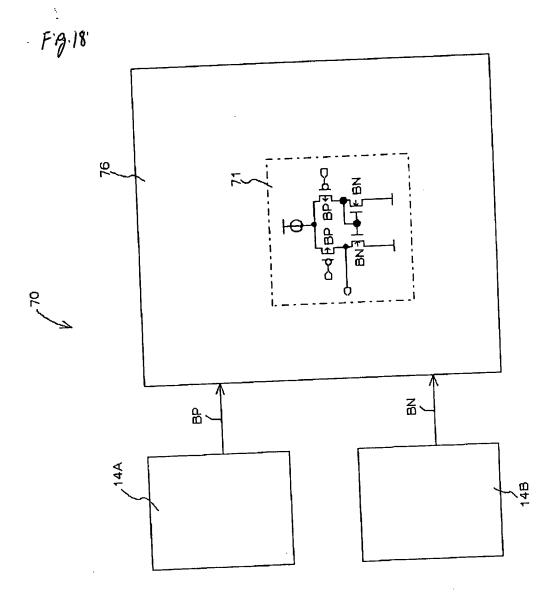
[F.g.13]

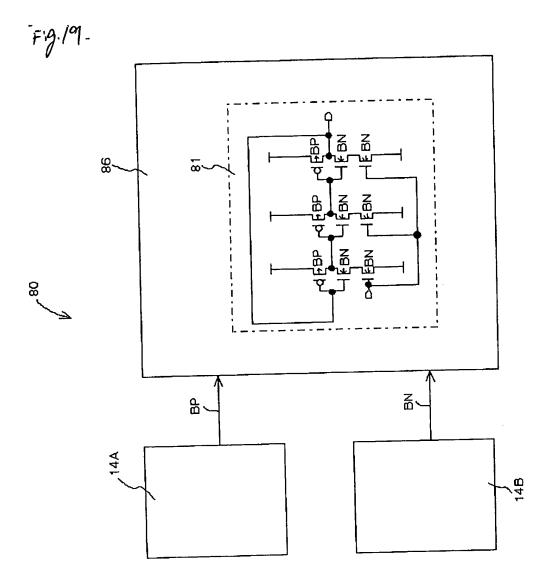


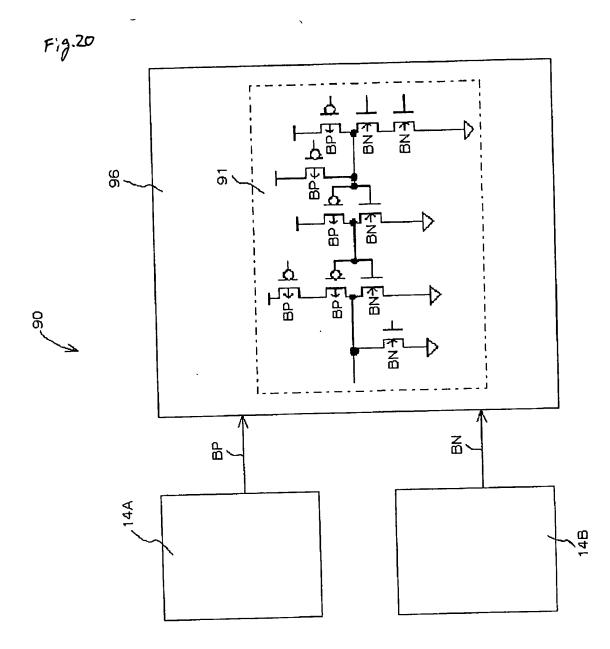
F17.14. -<u>m</u> ABP\_ Na L 9, 5, Na Na 550 윱, M N .14A 14B





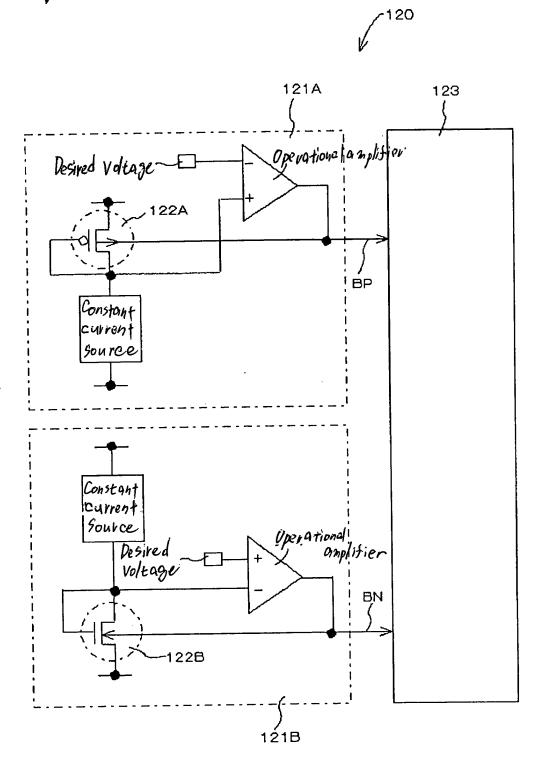


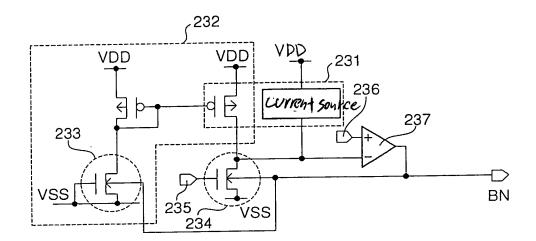


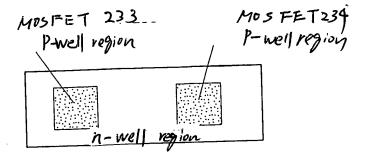


[Fig. 2] 106 100 8 8 <u>В</u>,

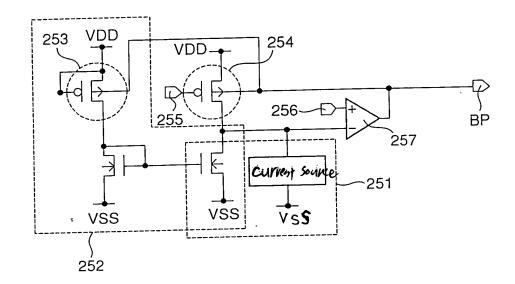
į

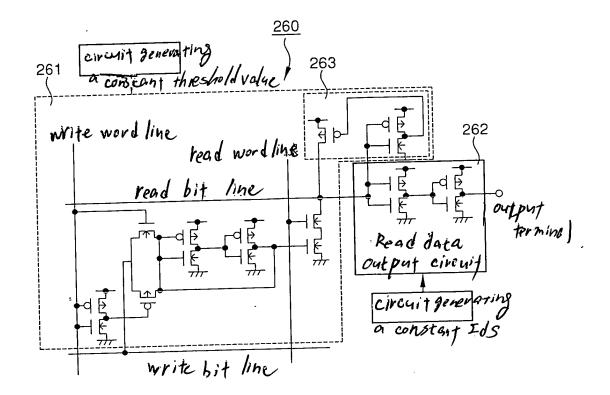


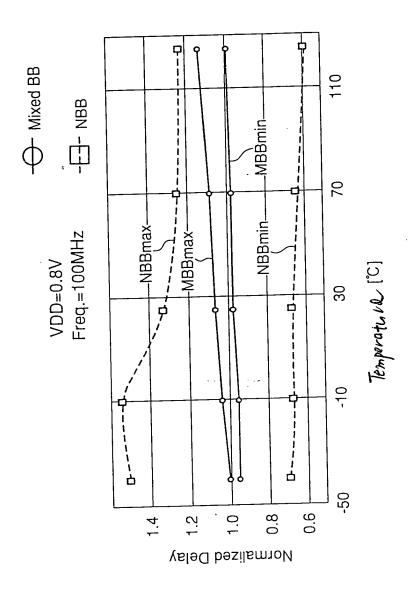


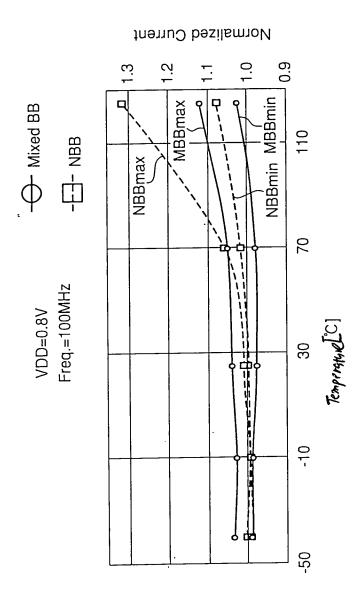


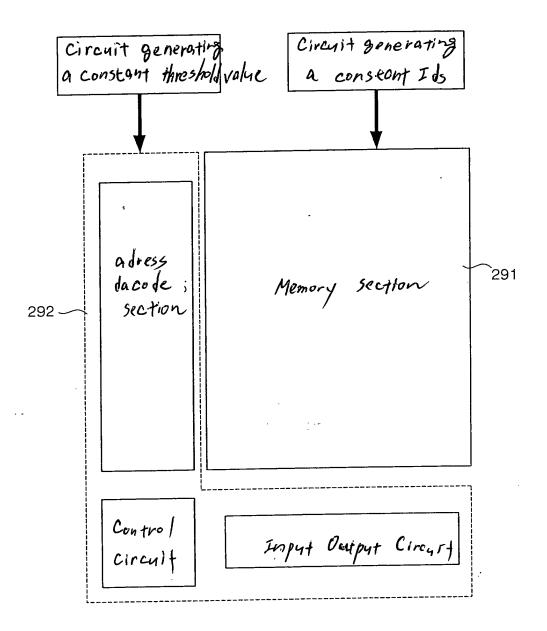
[Fig.25]

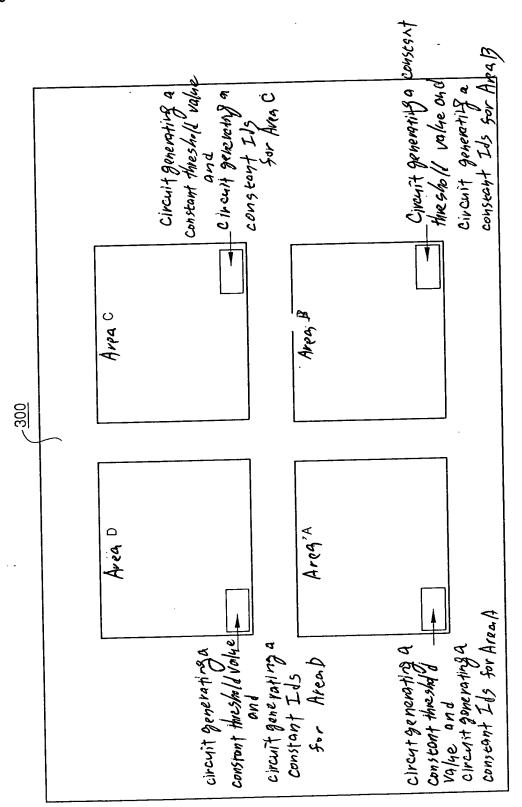


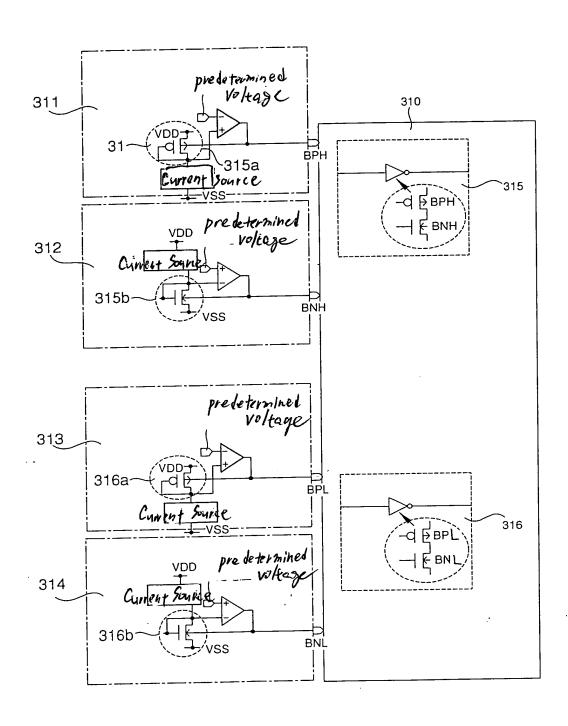


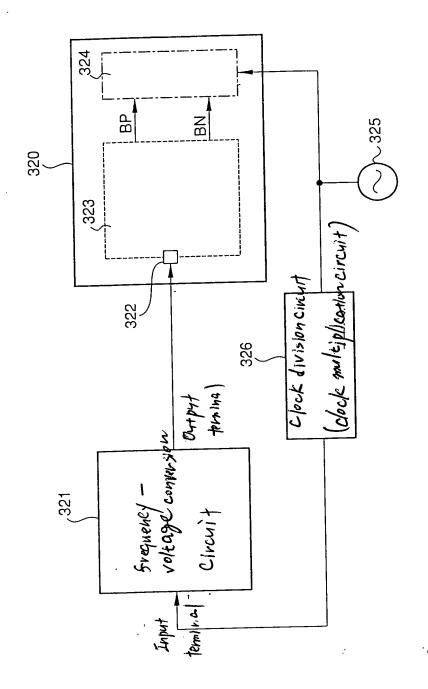


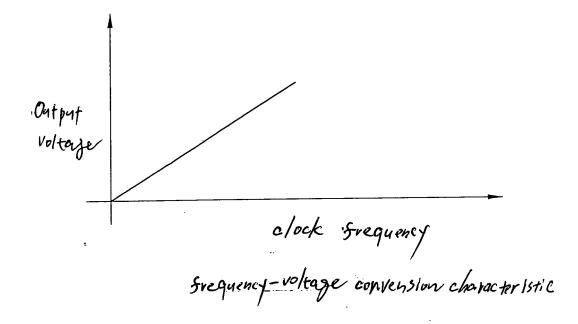


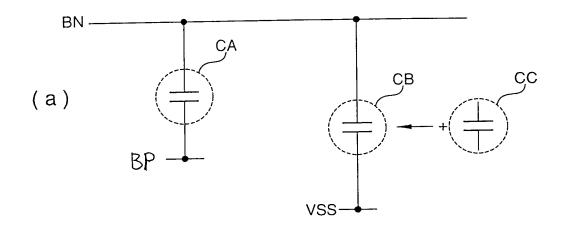


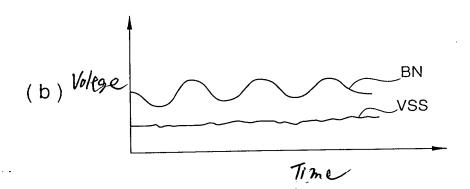












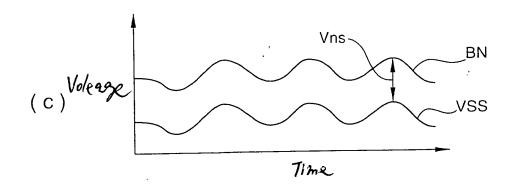
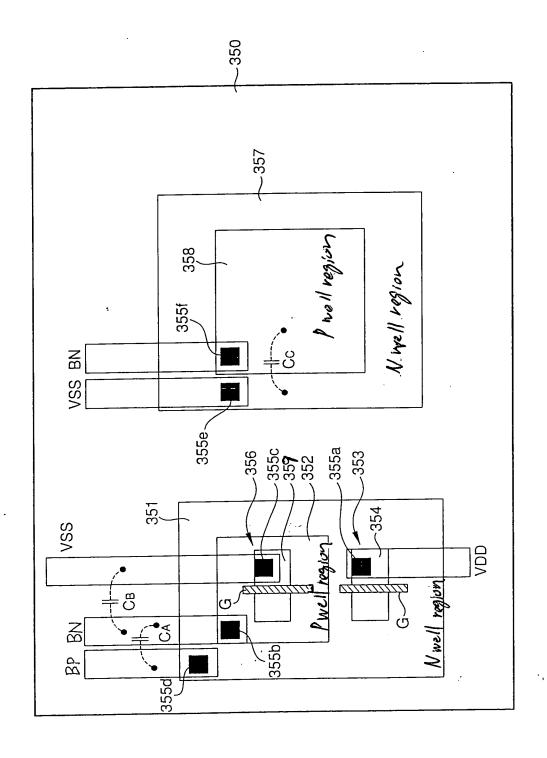
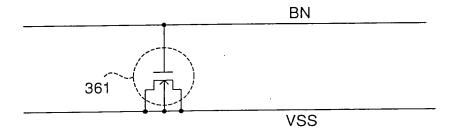
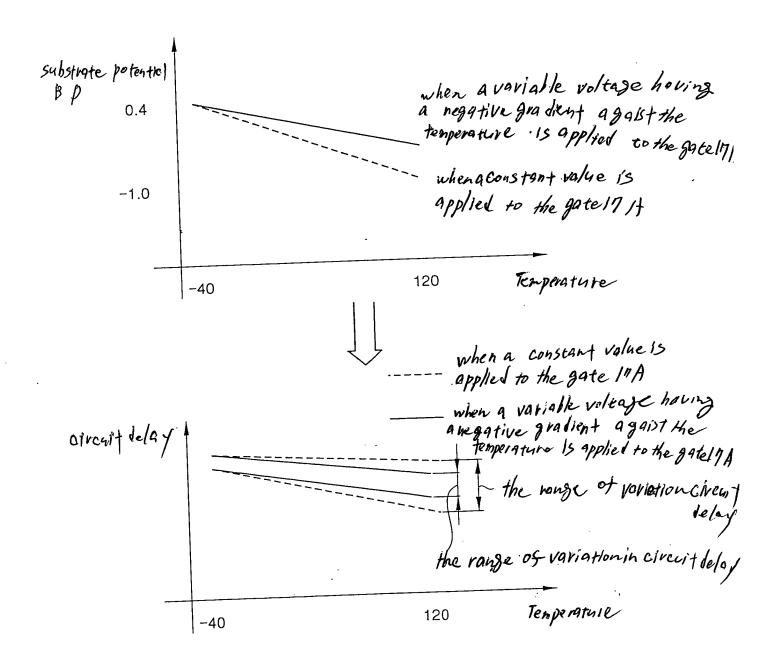


Fig.35







-[Fig.38]

